

Silicon NPN Power Transistors

2N6254

DESCRIPTION

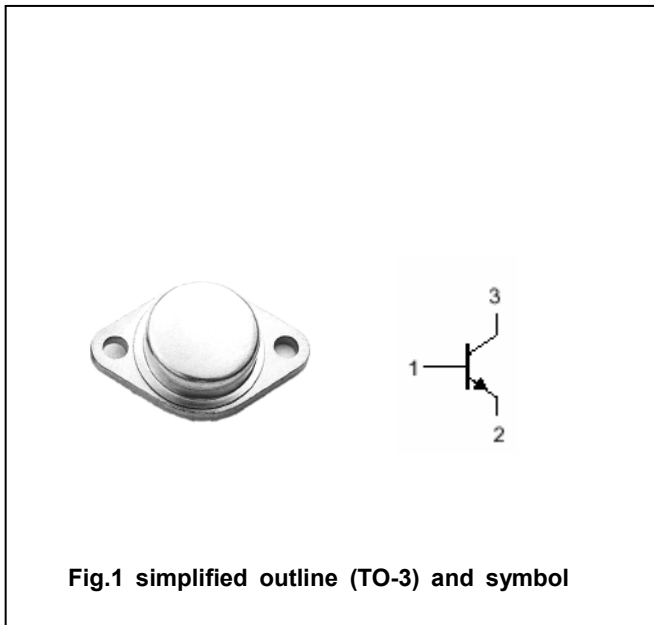
- With TO-3 package
- Low collector saturation voltage
- Wide safe operating area
- High dissipation capability

APPLICATIONS

- Series and shunt regulators
- High fidelity amplifiers
- Power switching circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		15	A
I _B	Base current		7	A
P _D	Total Power Dissipation	T _C =25□	150	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.17	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	80			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			0.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =15A ; I _B =3A			4.0	V
V _{BE}	Base-emitter on voltage	I _C =5A ; V _{CE} =2V			1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =60V ; I _B =0			1.0	mA
I _{CEX}	Collector cut-off current	V _{CE} =100V ; V _{BE} =-1.5V T _C =150 °C			0.5 5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			0.5	mA
h _{FE-1}	DC current gain	I _C =5A ; V _{CE} =2V	20		70	
h _{FE-2}	DC current gain	I _C =15A ; V _{CE} =4V	5			

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)